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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 1 of 2

Complete if Known	
Application Number	10/780,317
Filing Date	February 17, 2004
First Named Inventor	Volker HARLE
Art Unit	
Examiner Name	
Attorney Docket Number	5367-69

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind-Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
CK		US-5,831,277	11-03-1998	Razeghi	
CK		US-5,684,309	11-04-1997	McIntosh et al.	
CK		US-6,172,381 B1	01-09-2001	Nagahama et al.	
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Examiner Initials*	Cite No.[1]	Foreign Patent Document Country Code[3]-Number[4]-Kind-Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
CK		WO 98/31055	07-16-1998	Nagahama et a.		
CK		WO 01/39282	05-31-2001	Harle et al.		Abstract
CK		EP 1 017 133	07-05-2000	Hattori et al.		
CK		EP 1 263 031 A1	04-12-2002	Koike et al		

Examiner Signature	Christy Kovacek	Date Considered	6/15/05

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	Examiner Name	
Sheet 2 of 2	Attorney Docket Number	5367-69

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
CK	1.	Y.H. Song et al.: "Lateral Epitaxial Overgrowth of GaN and Its Crystallographic Tilt Depending on the Growth Condition", Phys. Stat. Sol. (a) 180, (2000), pp. 247-250	
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CK	4.	E. Feltin et al.: "Epitaxial Lateral Overgrowth of GaN on Silicon (111)", Phys. Stat. Sol. (a) 188, No. 2, pp. 733-737 (2001).	
CK	5.	T. Gehrke et al.: "Pendeo-Epitaxy of Gallium Nitride and Aluminum Nitride Films and Heterostructures on Silicon Carbide Substrate", MRS Internet J. Semicond. Res. 4S1, G3.2 (1999).	
CK	6.	P.R. Hagemann, et al.: "Improvement of the Optical and Structural Properties of MOCVD Grown GaN on Sapphire by an in-situ SiN Treatment", Phys. Stat. Sol. (a) 188, No. 2, (2001), pp. 659-662.	
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CK	10.	T. Wang et al.:; "A new method for a great reduction of dislocation density in a GaN layer grown on a sapphire substrate", Journal of Crystal Growth 213 (2000), pp. 188-192.	
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CK	12.	K. J. Linthicum et al.: "Process Routes for Low Defect-Density GaN on Various Substrates Employing PENDEO-Epitaxial Growth Techniques", MRS Internet J. Nitride Semicond. Res. 4S1, G4.9 (1999)	

Examiner Signature	Christy Kovacek	Date Considered	6/15/05

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